


Introduction to CMOS VLSI Design

Lecture 1: Circuits & Layout

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Outline

- ❑ A Brief History
- ❑ CMOS Gate Design
- ❑ Pass Transistors
- ❑ CMOS Latches & Flip-Flops
- ❑ Standard Cell Layouts
- ❑ Stick Diagrams

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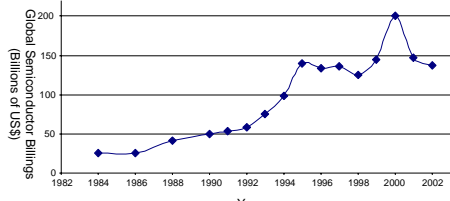
A Brief History

- ❑ 1958: First integrated circuit
 - Flip-flop using two transistors
 - Built by Jack Kilby at Texas Instruments
- ❑ 2003
 - Intel Pentium 4 μ processor (55 million transistors)
 - 512 Mbit DRAM (> 0.5 billion transistors)
- ❑ 53% compound annual growth rate over 45 years
 - No other technology has grown so fast so long
- ❑ Driven by miniaturization of transistors
 - Smaller is cheaper, faster, lower in power!
 - Revolutionary effects on society

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Annual Sales

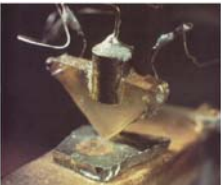
- ❑ 10^{18} transistors manufactured in 2003
 - 100 million for every human on the planet



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Invention of the Transistor

- ❑ Vacuum tubes ruled in first half of 20th century
 - Large, expensive, power-hungry, unreliable
- ❑ 1947: first point contact transistor
 - John Bardeen and Walter Brattain at Bell Labs
 - Read *Crystal Fire* by Riordan, Hoddeson



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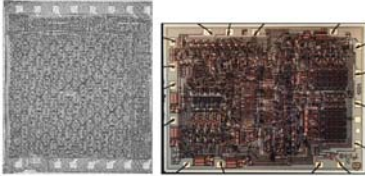
Transistor Types

- ❑ Bipolar transistors
 - npn or pnp silicon structure
 - Small current into very thin base layer controls large currents between emitter and collector
 - Base currents limit integration density
- ❑ Metal Oxide Semiconductor Field Effect Transistors
 - nMOS and pMOS MOSFETS
 - Voltage applied to insulated gate controls current between source and drain
 - Low power allows very high integration

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MOS Integrated Circuits

- 1970's processes usually had only nMOS transistors
 - Inexpensive, but consume power while idle

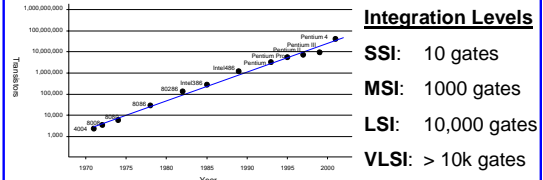


Intel 1101 256-bit SRAM Intel 4004 4-bit μ Proc

- 1980s-present: CMOS processes for low idle power

Moore's Law

- 1965: Gordon Moore plotted transistor on each chip
 - Fit straight line on semilog scale
 - Transistor counts have doubled every 26 months

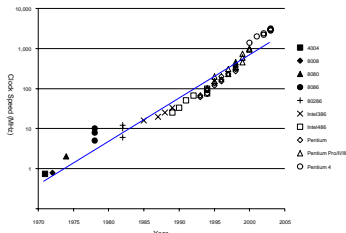


Integration Levels

- SSI: 10 gates
- MSI: 1000 gates
- LSI: 10,000 gates
- VLSI: > 10k gates

Corollaries

- Many other factors grow exponentially
 - Ex: clock frequency, processor performance

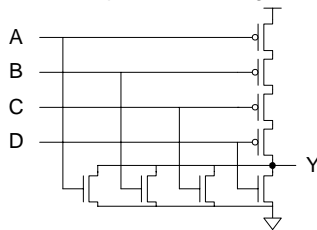


CMOS Gate Design

- Activity:
 - Sketch a 4-input CMOS NAND gate

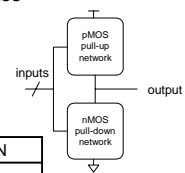
CMOS Gate Design

- Activity:
 - Sketch a 4-input CMOS NOR gate



Complementary CMOS

- Complementary CMOS logic gates
 - nMOS pull-down network
 - pMOS pull-up network
 - a.k.a. static CMOS



	Pull-up OFF	Pull-up ON
Pull-down OFF	Z (float)	1
Pull-down ON	0	X (crowbar)

Series and Parallel

- ❑ nMOS: 1 = ON
- ❑ pMOS: 0 = ON
- ❑ *Series*: both must be ON
- ❑ *Parallel*: either can be ON

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Conduction Complement

- ❑ Complementary CMOS gates always produce 0 or 1
- ❑ Ex: NAND gate
 - Series nMOS: $Y=0$ when both inputs are 1
 - Thus $Y=1$ when either input is 0
 - Requires parallel pMOS
- ❑ Rule of *Conduction Complements*
 - Pull-up network is dual of pull-down
 - Parallel -> series, series -> parallel

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Compound Gates

- ❑ *Compound gates* can do any inverting function
- ❑ Ex: $Y = \overline{A}B + C\overline{D}$ (AND-AND-OR-INVERT, AOI22)

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Example: O3AI

- ❑ $Y = \overline{(A+B+C)}\overline{D}$

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Example: O3AI

- ❑ $Y = \overline{(A+B+C)}\overline{D}$

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

Signal Strength

- ❑ *Strength* of signal
 - How close it approximates ideal voltage source
- ❑ V_{DD} and GND rails are strongest 1 and 0
- ❑ nMOS pass strong 0
 - But degraded or weak 1
- ❑ pMOS pass strong 1
 - But degraded or weak 0
- ❑ Thus nMOS are best for pull-down network

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Pass Transistors



- Transistors can be used as switches


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Pass Transistors


- Transistors can be used as switches

$g = 0$



$g = 1$




Input $g = 1$ Output

0 → strong 0


$g = 1$

1 → degraded 1

$g = 0$



$g = 1$



Input $g = 0$ Output

0 → degraded 0

$g = 0$

→ strong 1

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
Transmission Gates

- Pass transistors produce degraded outputs
- Transmission gates* pass both 0 and 1 well


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Transmission Gates


- Pass transistors produce degraded outputs
- Transmission gates* pass both 0 and 1 well



$g = 0, gb = 1$



$g = 1, gb = 0$






Input Output

$g = 1, gb = 0$

0 → strong 0

$g = 1, gb = 0$

1 → strong 1

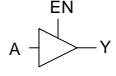
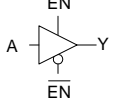




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Tristates

- Tristate buffer* produces Z when not enabled

EN	A	Y
0	0	
0	1	
1	0	
1	1	

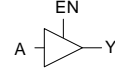
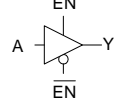



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Tristates

- Tristate buffer* produces Z when not enabled

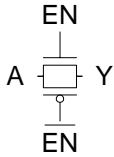
EN	A	Y
0	0	Z
0	1	Z
1	0	0
1	1	1

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Nonrestoring Tristate

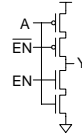
- Transmission gate acts as tristate buffer
 - Only two transistors
 - But *nonrestoring*
 - Noise on A is passed on to Y



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Tristate Inverter

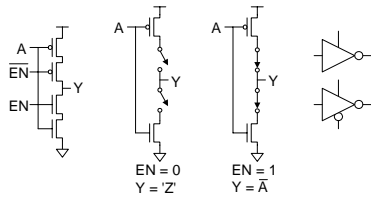
- Tristate inverter produces restored output
 - Violates conduction complement rule
 - Because we want a Z output



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Tristate Inverter

- Tristate inverter produces restored output
 - Violates conduction complement rule
 - Because we want a Z output

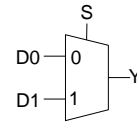


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Multiplexers

- 2:1 multiplexer chooses between two inputs

S	D1	D0	Y
0	X	0	
0	X	1	
1	0	X	
1	1	X	

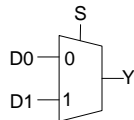


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Multiplexers

- 2:1 multiplexer chooses between two inputs

S	D1	D0	Y
0	X	0	0
0	X	1	1
1	0	X	0
1	1	X	1



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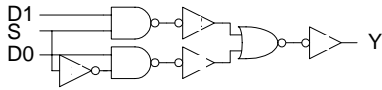
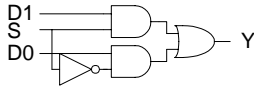
Gate-Level Mux Design

- $Y = SD_1 + \bar{S}D_0$ (too many transistors)
- How many transistors are needed?

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Gate-Level Mux Design

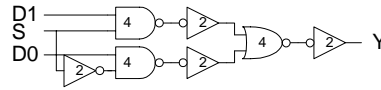
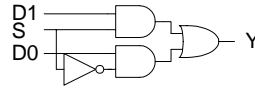
- ❑ $Y = SD_1 + \bar{S}D_0$ (too many transistors)
- ❑ How many transistors are needed?



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Gate-Level Mux Design

- ❑ $Y = SD_1 + \bar{S}D_0$ (too many transistors)
- ❑ How many transistors are needed? 20



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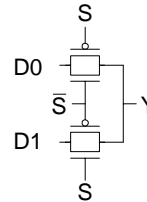
Transmission Gate Mux

- ❑ Nonrestoring mux uses two transmission gates

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Transmission Gate Mux

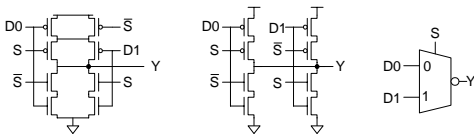
- ❑ Nonrestoring mux uses two transmission gates
 - Only 4 transistors



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Inverting Mux

- ❑ Inverting multiplexer
 - Use compound AOI22
 - Or pair of tristate inverters
 - Essentially the same thing
- ❑ Noninverting multiplexer adds an inverter



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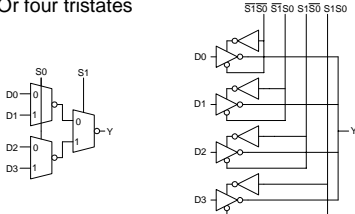
4:1 Multiplexer

- ❑ 4:1 mux chooses one of 4 inputs using two selects

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4:1 Multiplexer

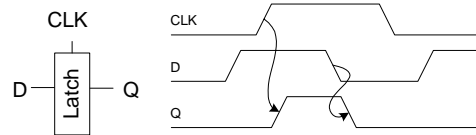
- 4:1 mux chooses one of 4 inputs using two selects
 - Two levels of 2:1 muxes
 - Or four tristates



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D Latch

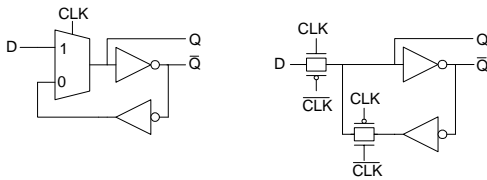
- When CLK = 1, latch is *transparent*
 - D flows through to Q like a buffer
- When CLK = 0, the latch is *opaque*
 - Q holds its old value independent of D
- a.k.a. *transparent latch* or *level-sensitive latch*



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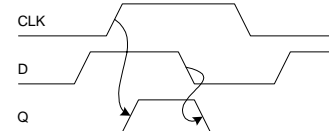
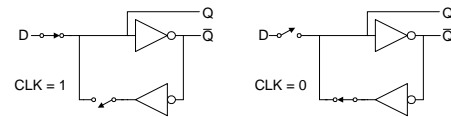
D Latch Design

- Multiplexer chooses D or old Q



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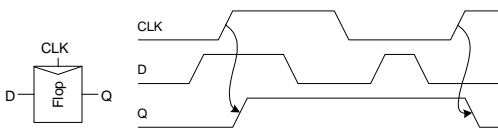
D Latch Operation



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D Flip-flop

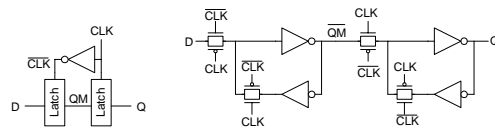
- When CLK rises, D is copied to Q
- At all other times, Q holds its value
- a.k.a. *positive edge-triggered flip-flop*, *master-slave flip-flop*



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D Flip-flop Design

- Built from master and slave D latches



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D Flip-flop Operation

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Race Condition

- ❑ Back-to-back flops can malfunction from clock skew
 - Second flip-flop fires late
 - Sees first flip-flop change and captures its result
 - Called *hold-time failure* or *race condition*

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Nonoverlapping Clocks

- ❑ Nonoverlapping clocks can prevent races
 - As long as nonoverlap exceeds clock skew
- ❑ You can use them if you like for safe design
 - Industry manages skew more carefully instead

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